

L Number	Hits	Search Text	DB	Time stamp
1	1	"20030001222"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 09:19
14	316	air near2 (gap\$1 hole\$1 insulat\$4 dielectric space\$1) with (over overlap\$4) with (gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 10:20
21	734	air near2 (gap\$1 hole\$1 insulat\$4 dielectric space\$1) with (gate )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 10:46
28	682	(air near2 (gap\$1 hole\$1 insulat\$4 dielectric space\$1) with (gate )) not (air near2 (gap\$1 hole\$1 insulat\$4 dielectric space\$1) with (over overlap\$4) with (gate electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 10:22
35	133	((air near2 (gap\$1 hole\$1 insulat\$4 dielectric space\$1) with (gate )) not (air near2 (gap\$1 hole\$1 insulat\$4 dielectric space\$1) with (over overlap\$4) with (gate electrode))) and (438/\$6 257/\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:22
42	81	air near2 (gap\$1 hole\$1 insulat\$4 dielectric space\$1) with (transistor ) and (438/\$6 257/\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 10:53
49	68	air with (transistor gate electrode) with (overlap\$4 cross crossover intersection) and (438/\$6 257/\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 10:59
60	0	buried near insulator with ("3" "5") with (micron ".mu." mu micrometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:20
67	132	insulator with ("3" "5") with (micron ".mu." mu micrometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 13:26
74	0	((257/443, 448).CCLS.) and (insulator with ("3" "5") with (micron ".mu." mu micrometer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:21
81	42	(insulator with ("3" "5") with (micron ".mu." mu micrometer)) and (438/\$6 257/\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:25
88	0	((insulator with ("3" "5") with (micron ".mu." mu micrometer)) and (438/\$6 257/\$6)) and bisbenzocyclobutene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:24
95	0	bisbenzocyclobutene with ("3" "5") with (micron ".mu." mu micrometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:24
102	14	bisbenzocyclobutene and ("3" "5") with (micron ".mu." mu micrometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 13:33

109	0	(bisbenzocyclobutene and ("3" "5") with (micron ".mu." mu micrometer)) and (438/\$6 257/\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 13:32
116	249	dielectric with ("3" "5") near2 (micron ".mu." mu micrometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 13:27
123	26	(dielectric with ("3" "5") near2 (micron ".mu." mu micrometer)) and (438/\$6 257/\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 13:59
130	2	("5623161").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 13:59